LC378100QM, QT



8 MEG (1048576 words × 8 bits) Mask ROM Internal Clocked Silicon Gate

Preliminary

Overview

The LC378100QM and LC378100QT are 1,048,576-word \times 8-bit organization (8,388,608-bit) mask programmable read only memories. They feature a wide operating voltage range (2.6 to 5.5 V), a 100-ns access time (t_{CA}) at V_{CC} = 4.5 to 5.5 V, and a 200-ns access time at V_{CC} = 2.6 to 3.3 V. Thus these LSIs can be used in a wide range of systems, from 5-V systems that require high-speed access to 3-V systems that use batteries.

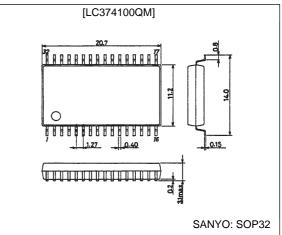
Features

- 1048576 words × 8 bits organization
- Supply voltage range: 2.6 to 5.5
- Fast access time(t_{AA}): 120 ns (max.) $V_{CC} = 4.5$ to 5.5 V
 - (t_{CA}) : 100 ns (max.) V_{CC} = 4.5 to 5.5 V 200 ns (max.) V_{CC} = 2.6 to 5.5 V
 - current 55 mA (max.) $V_{CC} = 2.0$
- Operating current 55 mA (
- Standby current 30 µA (max.)
- Full static operation (internal clocked type)
- 3 state outputs
- JEDEC standard pin configuration
- Package type LC378100QM: SOP32 (525 mil) LC378100QT: TSOP32 (8 mm × 20 mm)

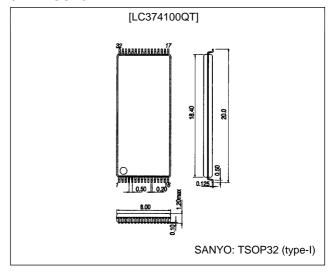
Package Dimensions

unit: mm



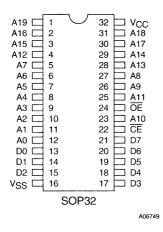


unit: mm 3224-TSOP32



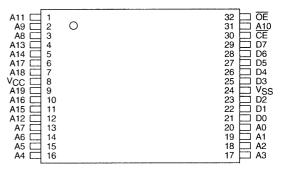
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Pin Assignments



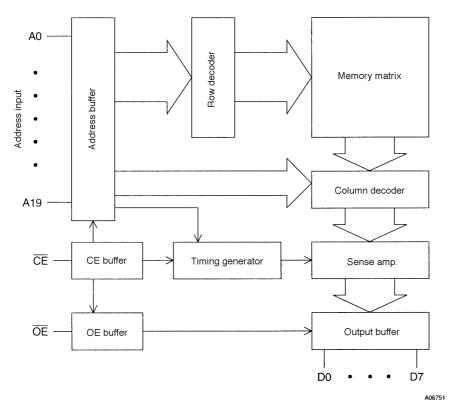
Pin Functions

A0 to A16	Address input
D0 to D7	Data output
CE	Chip enable input
ŌE	Output enable input
V _{CC}	Power supply
V _{SS}	Ground



TSOP32

Block Diagram



Truth Table

CE	ŌĒ	Output	Current drain		
Н	Х	X High-impedance Standby mode			
L	Н	High-impedance	Operating mode		
L	L	DOUT	Operating mode		

X: H or L level should be offered.

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Specifications Absolute Maximum Ratings *1

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	V _{cc}		-0.3 to +7.0	V
Supply input voltage	V _{IN}		-0.3*2 to V _{CC} + 0.3	V
Supply output voltage	V _{OUT}		-0.3 to V _{CC} + 0.3	V
Allowable power dissipation	Pd max	Ta = 25°C; Reference values for the SANYO DIP package	1.0	W
Operating temperature	Topr		-10 to +70	°C
Storage temperature	Tstg		-55 to +125	°C

Note: 1. Permanent device damage may occur if Absolute Maximum Ratings are exceeded. Functional operation should be restricted to Recommended Operating Conditions.

2. V_{IN} (min) = -3.0 V (pulse width \leq 30 ns)

Input/Output Capacitance* at Ta = 25°C, f = 1.0 MHz

Parameter	Symbol	Conditions		Unit		
Farameter	Symbol	Conditions	min	typ	max	
Input capacitance	CIN	$V_{IN} = 0$ V; Reference values for the SANYO DIP package			8	pF
Output capacitance	C _{OUT}	V_{OUT} = 0 V; Reference values for the SANYO DIP package			10	pF

Note: * This parameter is periodically sampled and not 100% tested.

DC Recommended Operating Ranges at Ta = –10 to +70°C, V_{CC} = 2.6 to 5.5 $\rm V$

Parameter	Symbol Conditions	Conditions	Ratings			Unit
		Conditions	min	typ	max	
Supply voltage	V _{CC}		2.6	5.0	5.5	V
Input high level voltage	V _{IH}		2.2		V _{CC} + 0.3	V
Input low level voltage	V _{IL}		-0.3		+0.6	V

DC Electrical Characteristics at Ta = –10 to +70°C, V_{CC} = 2.6 to 5.5 V

Parameter	Symbol	Conditions		- Unit		
	Symbol	Conditions	min	typ	max	Unit
Operating supply current	I _{CCA1}	$\overline{\text{CE}} = 0.2 \text{ V}, \text{ V}_{\text{I}} = \text{V}_{\text{CC}} - 0.2 \text{ V}/0.2 \text{ V}$			30	mA
Operating supply current	I _{CCA2}	$\overline{CE} = V_{IL}$, $I_O = 0$ mA, $V_I = V_{IH}/V_{IL}$, f = 10 MHz			55	mA
Standby supply current	I _{CCS1}	$\overline{CE} = V_{CC} - 0.2 V$			30 (1.0)	μA
	I _{CCS2}	CE = V _{IH}			1.0 (300)	mA(µA)
Input leakage current	ILI	$V_{IN} = 0$ to V_{CC}			±1.0	μA
Output leakage current	I _{LO}	\overline{CE} or $\overline{OE} = V_{IH}$, $V_{OUT} = 0$ to V_{CC}			±1.0	μA
Output high level voltage	V _{OH}	I _{OH} = -0.5 mA	0.8 V _{CC}			V
Output low level voltage	V _{OL}	I _{OL} = 0.5 mA			0.2	V

Note: * Guaranteed at Ta = 25°C

AC Characteristics at Ta = -10 to $+70^{\circ}$ C, V_{CC} = 2.6 to 5.5 V

Parameter	Symbol Conditions	Conditions		- Unit		
		min	typ	max		
Cycle time	t _{CYC}		200 (120)			ns
Address access time	t _{AA}				200 (120)	ns
CE access time	t _{CA}				200 (100)	ns
OE access time	t _{OA}				80 (40)	ns
Output hold time	t _{OH}		20			ns
Output disable time*1	t _{OD} *1				100	ns

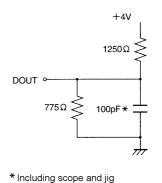
Note: 1. t_{OD} is measured from the earlier edge of the \overline{CE} or \overline{OE} 's going high impedance.

This parameter is periodically sampled and not 100% tested.

2. Guaranteed at V_{CC} = 4.5 to 5.5 V

AC Test Conditions

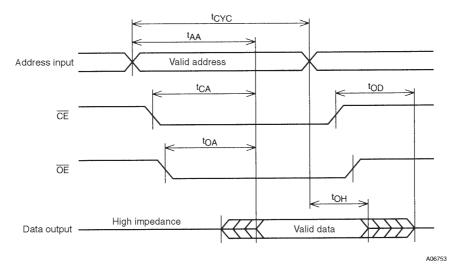
Input pulse levels	0.4 to 2.8 V
Input rise/fall time	5 ns
Input timing level	1.5 V
Output timing level	1.5 V
Output load	See Figure 1



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Timing Chart



System Design Notes

These LSIs adopt the ATD technique, in which operation starts when a change in either the \overline{CE} or address inputs is detected. This means that the output data immediately after power is applied is invalid. When using these LSIs as program memory for Z80 and similar microprocessors, applications must take into account the fact that valid data will not be output after power is first applied unless the value of either the \overline{CE} or at least one of the address lines is changed after the power supply has stabilized.

Another point due to the use of the ATD technique is that these LSIs are sensitive to input noise. Do not apply voltages outside the allowable DC input levels for extended periods and do not apply input voltages with large noise components.

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